## **DATA SHEET**



## **GaAs INTEGRATED CIRCUIT**

# $\mu$ PG2126TB

#### L-BAND PA DRIVER AMPLIFIER

#### **DESCRIPTION**

The  $\mu$ PG2126TB is a GaAs MMIC for PA driver amplifier which were developed for dual band mobile phone and another L-band application. The device can operate with 3.6 V TYP., having the high gain and low distortion.

#### **FEATURES**

Supply voltage : VDD1, 2, 3 = 3.1 to 4.4 V (3.6 V TYP.)

★ • Low operation current : IDD1 = 16 mA TYP. @ VDD1 = 3.6 V, f = 925 MHz, Pout = +8 dBm

 $\star$  : IDD2 = 28 mA TYP. @ VDD2, 3 = 3.6 V, f = 1 441 MHz, Pout = +8 dBm

★ • High power gain
 : G<sub>P1</sub> = 16 dB TYP. @ V<sub>DD1</sub> = 3.6 V, f = 925 MHz, P<sub>in</sub> = -10 dBm
 : G<sub>P2</sub> = 26 dB TYP. @ V<sub>DD2</sub>, 3 = 3.6 V, f = 1 441 MHz, P<sub>in</sub> = -22 dBm

• Low distortion : Padj1 = -60 dBc TYP. @ VDD1, 2, 3 = 3.6 V, f = 925 MHz, 1 441 MHz, Pout = +8 dBm,

 $\Delta f = \pm 50 \text{ kHz}$ , 21 kHz Bandwidth.

High-density surface mounting: 6-pin super minimold package (2.0 × 1.25 × 0.9 mm)

#### **APPLICATION**

• Digital Cellular: dual band mobile phone etc.

#### ORDERING INFORMATION

Part Number	Package	Marking	Supplying Form
μPG2126TB-E3	6-pin super minimold	G2K	<ul> <li>Embossed tape 8 mm wide</li> <li>Pin 1, 2, 3 face the perforation side of the tape</li> <li>Qty 3 kpcs/reel</li> </ul>

Remark To order evaluation samples, contact your nearby sales office.

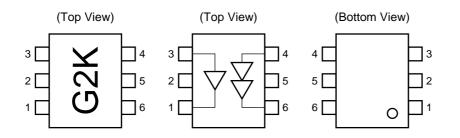
Part number for sample order: μPG2126TB

#### Caution Electro-static sensitive devices

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Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

## PIN CONNECTIONS, MARKING AND INTERNAL BLOCK DIAGRAM



Pin No.	Pin Name	
1	V <sub>DD1</sub> /OUTPUT1	
2	GND	
3	INPUT1	
4	INPUT2	
5	V <sub>DD2</sub>	
6	V <sub>DD3</sub> /OUTPUT2	

## ABSOLUTE MAXIMUM RATINGS (Unless otherwise specified, TA = +25°C)

Parameter	Symbol	Ratings	Unit
Supply Voltage1, 2, 3	V <sub>DD1, 2, 3</sub>	6.0	V
Input Power 1 (INPUT1)	P <sub>in1</sub>	+4	dBm
Input Power 2 (INPUT2)	P <sub>in2</sub>	-4	dBm
Power Dissipation	P□	140 Note	mW
Operating Ambient Temperature	TA	-30 to +90	°C
Storage Temperature	T <sub>stg</sub>	−35 to +150	°C

**Note** Mounted on double copper-clad  $50 \times 50 \times 1.6$  mm epoxy glass PWB,  $T_A = +85^{\circ}C$ 

### RECOMMENDED OPERATING RENGE (TA = +25°C)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage1, 2, 3	V <sub>DD1, 2, 3</sub>	3.1	3.6	4.4	V
Input Power 1 (INPUT1)	P <sub>in1</sub>	-	-	-10	dBm
Input Power 2 (INPUT2)	P <sub>in2</sub>	-	_	-20	dBm
Operating Frequency 1	f <sub>opt1</sub>	893	-	960	MHz
Operating Frequency 2	f <sub>opt2</sub>	1 429	_	1 453	MHz

#### **ELECTRICAL CHARACTERISTICS -INPUT1-OUTPUT1-**

(Unless otherwise specified,  $T_A = +25$ °C,  $V_{DD1} = 3.6$  V,  $\pi/4DQPSK$  modulated signal input, External input and output matching)

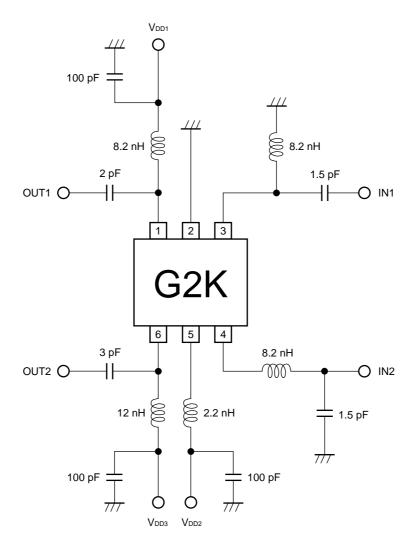
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Operating Frequency 1	f <sub>opt1</sub>		893	925	960	MHz
Power Gain 1	G <sub>P1</sub>	$P_{in} = -10 \text{ dBm}$	14	16	18	dB
Circuit Current 1	I <sub>DD1</sub>	Pout = +8 dBm		16	20	mA
Adjacent Channel Power Leakage 1	P <sub>adj1</sub>	$P_{out} = +8 \text{ dBm},$ $\Delta f = \pm 50 \text{ kHz}, 21 \text{ kHz Bandwidth}$	-	-60	-55	dBc
Adjacent Channel Power Leakage 2	P <sub>adj2</sub>	Pout = +8 dBm, $\Delta f = \pm 100$ kHz, 21 kHz Bandwidth	1	-70	-65	dBc

#### **ELECTRICAL CHARACTERISTICS -INPUT2-OUTPUT2-**

(Unless otherwise specified,  $T_A = +25^{\circ}\text{C}$ ,  $V_{DD2} = V_{DD3} = 3.6 \text{ V}$ ,  $\pi/4\text{DQPSK}$  modulated signal input, External input and output matching)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Operating Frequency 2	f <sub>opt2</sub>		1 429	1 441	1 453	MHz
Power Gain 2	G <sub>P2</sub>	P <sub>in</sub> = -22 dBm	24	26	28	dB
Circuit Current 2	I <sub>DD2</sub>	Pout = +8 dBm	-	28	32	mA
Adjacent Channel Power Leakage 3	P <sub>adj</sub> 3	Pout = +8 dBm, $\Delta f = \pm 50$ kHz, 21 kHz Bandwidth	-	-60	-55	dBc
Adjacent Channel Power Leakage 4	P <sub>adj4</sub>	Pout = +8 dBm, $\Delta f = \pm 100$ kHz, 21 kHz Bandwidth	ı	-70	-65	dBc

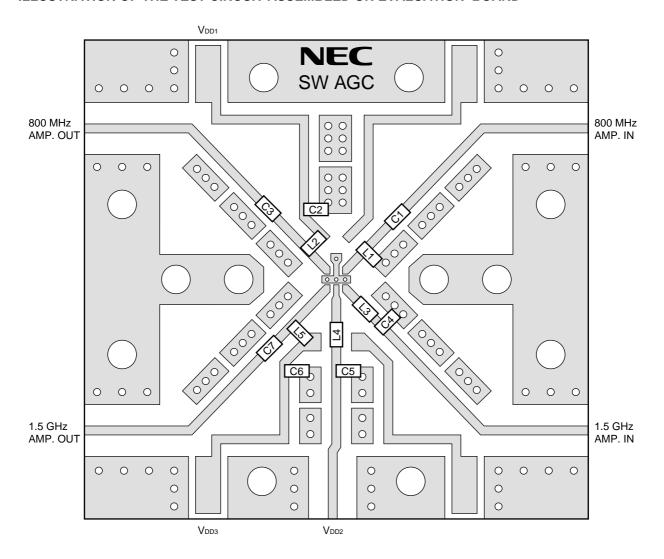
## EVALUATION CIRCUIT (VDD1, 2, 3 = 3.6 V, f = 925 MHz (INPUT1-OUTPUT1), f = 1 441 MHz (INPUT2-OUTPUT2))



The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.



#### ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



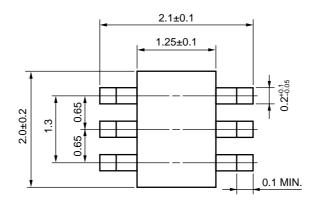
#### **COMPONENT LIST**

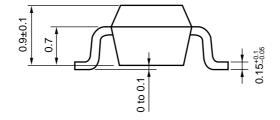
Symbol	Rating	Part Number	Munufacturer
L1, L2, L3	8.2 nH	TFL0816-8N2	Susumu
L4	2.2 nH	TFL0816-2N2	Susumu
L5	12 nH	TFL0816-12N	Susumu
C1, C4	1.5 pF	GRM39CK1R5C50	muRata
C2, C5, C6	100 pF	GRM39CH101J50	muRata
C3	2 pF	GRM39CK020C50	muRata
C7	3 pF	GRM39CJ030C50	muRata

5

## PACKAGE DIMENSIONS

## 6-PIN SUPER MINIMOLD (UNIT: mm)







#### RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol	
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) Time at temperature of 200°C or higher Preheating time at 120 to 150°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 215°C or below : 25 to 40 seconds : 30 to 60 seconds : 3 times : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).

7

NEC  $\mu$ PG2126TB

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#### SAFETY INFORMATION ON THIS PRODUCT

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GaAs Products

The product contains gallium arsenide, GaAs.

GaAs vapor and powder are hazardous to human health if inhaled or ingested.

- Do not destroy or burn the product.
- Do not cut or cleave off any part of the product.
- Do not crush or chemically dissolve the product.
- Do not put the product in the mouth.

Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.

#### ▶Business issue

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#### ▶Technical issue

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